

PSMN012-80BS

N-channel 80 V 11 mΩ standard level MOSFET in D2PAK Rev. 2 — 1 March 2012 Product data

Product data sheet

Product profile 1.

1.1 General description

Standard level N-channel MOSFET in D2PAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------------|--|--|-----|-----|-----|------|
| V_{DS} | drain-source voltage | T _j ≥ 25 °C; T _j ≤ 175 °C | - | - | 80 | V |
| I_D | drain current | $T_{mb} = 25 ^{\circ}C; V_{GS} = 10 V; \text{see } \underline{\text{Figure 1}}$ | - | - | 74 | Α |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; see <u>Figure 2</u> | - | - | 148 | W |
| Tj | junction temperature | | -55 | - | 175 | °C |
| Static char | racteristics | | | | | |
| R _{DSon} | drain-source on-state resistance | $V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ °C}$ | - | 9 | 11 | mΩ |
| Dynamic o | haracteristics | | | | | |
| Q_{GD} | gate-drain charge | $V_{GS} = 10 \text{ V}$; $I_D = 25 \text{ A}$; $V_{DS} = 40 \text{ V}$; see Figure 14; see Figure 15 | - | 9.4 | - | nC |
| Avalanche | ruggedness | | | | | |
| E _{DS(AL)S} | non-repetitive drain-source avalanche energy | V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 74 A; V_{sup} ≤ 80 V; R_{GS} = 50 Ω ; unclamped | - | - | 100 | mJ |



2. Pinning information

Table 2. Pinning information

| | | <u> </u> | | | | |
|-----|--------|-----------------------------------|--------------------|----------------|--|--|
| Pin | Symbol | Description | Simplified outline | Graphic symbol | | |
| 1 | G | gate | | _ | | |
| 2 | D | drain[1] | mb | D D | | |
| 3 | S | source | | 。 (兵才) | | |
| mb | D | nounting base; connected to drain | | mbb076 S | | |
| | | | SOT404 (D2PAK) | | | |

^[1] It is not possible to make connection to pin 2

3. Ordering information

Table 3. Ordering information

| Type number | Package | | |
|--------------|---------|--|---------|
| | Name | Description | Version |
| PSMN012-80BS | D2PAK | plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped) | SOT404 |

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|----------------------|--|--|-----|-----|------|
| V_{DS} | drain-source voltage | T _j ≥ 25 °C; T _j ≤ 175 °C | - | 80 | V |
| V_{DGR} | drain-gate voltage | $T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$ | - | 80 | V |
| V_{GS} | gate-source voltage | | -20 | 20 | V |
| I_D | drain current | $V_{GS} = 10 \text{ V}; T_{mb} = 100 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$ | - | 52 | Α |
| | | V _{GS} = 10 V; T _{mb} = 25 °C; see <u>Figure 1</u> | - | 74 | Α |
| I _{DM} | peak drain current | pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 \text{ °C}$; see Figure 3 | - | 295 | Α |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; see <u>Figure 2</u> | - | 148 | W |
| T _{stg} | storage temperature | | -55 | 175 | °C |
| Tj | junction temperature | | -55 | 175 | °C |
| $T_{sld(M)}$ | peak soldering temperature | | - | 260 | °C |
| Source-drain | n diode | | | | |
| Is | source current | T _{mb} = 25 °C | - | 74 | Α |
| I _{SM} | peak source current | pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$ | - | 295 | Α |
| Avalanche r | uggedness | | | | |
| E _{DS(AL)S} | non-repetitive drain-source avalanche energy | V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 74 A; V_{sup} ≤ 80 V; R_{GS} = 50 Ω ; unclamped | - | 100 | mJ |

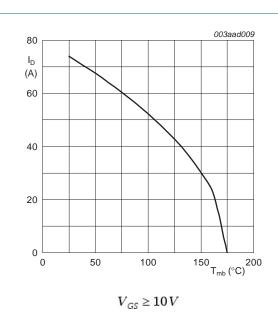


Fig 1. Continuous drain current as a function of mounting base temperature

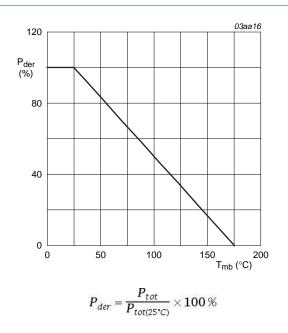
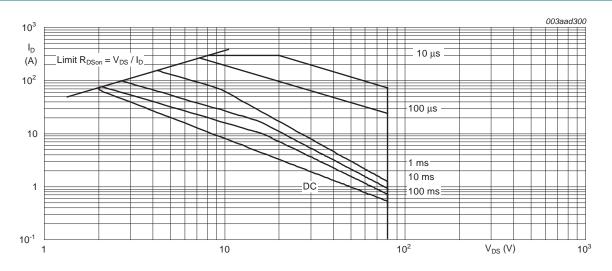


Fig 2. Normalized total power dissipation as a function of mounting base temperature



 $T_{mb} = 25^{\circ}C$; I_{DM} is a single pulse

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------|---|---|-----|------|-----|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | see Figure 4 | - | 0.65 | 1 | K/W |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | minimum footprint; mounted on a circuit board | - | 50 | - | K/W |

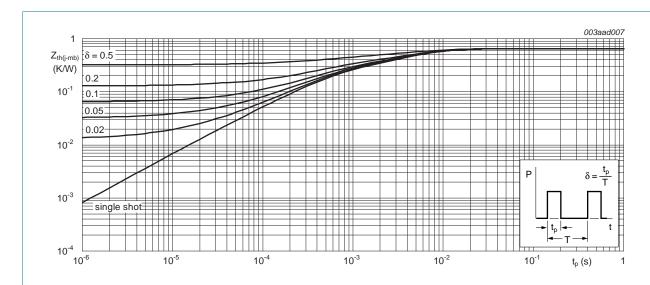


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration; typical values

6. Characteristics

Table 6. Characteristics

Tested to JEDEC standards where applicable.

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|---|-----------------------------------|---|-----|------|-----|-----------|
| Static char | acteristics | | | | | |
| V _{(BR)DSS} drain-source breakdown voltage | | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$ | 73 | - | - | V |
| | | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$ | 80 | - | - | V |
| $V_{GS(th)}$ | gate-source threshold voltage | $I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 175$ °C; see Figure 11; see Figure 12 | 1 | - | - | V |
| | | $I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = -55$ °C; see Figure 11; see Figure 12 | - | - | 4.6 | V |
| | | $I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 25$ °C; see <u>Figure 11</u> ; see <u>Figure 12</u> | 2 | 3 | 4 | V |
| I _{DSS} | drain leakage current | $V_{DS} = 80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$ | - | - | 3 | μA |
| | | V _{DS} = 80 V; V _{GS} = 0 V; T _j = 125 °C | - | - | 60 | μΑ |
| I _{GSS} | gate leakage current | $V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$ | - | - | 100 | nA |
| | | $V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$ | - | - | 100 | nA |
| R _{DSon} | drain-source on-state resistance | $V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 100 \text{ °C};$ see Figure 13 | - | - | 18 | mΩ |
| | | V _{GS} = 10 V; I _D = 15 A; T _j = 25 °C | - | 9 | 11 | $m\Omega$ |
| R _G | internal gate resistance (AC) | f = 1 MHz | - | 0.97 | - | Ω |
| Dynamic c | haracteristics | | | | | |
| Q _{G(tot)} | total gate charge | $I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V$ | - | 36 | - | nC |
| | | $I_D = 25 \text{ A}; V_{DS} = 40 \text{ V}; V_{GS} = 10 \text{ V};$ | - | 43 | - | nC |
| Q_GS | gate-source charge | see Figure 14; see Figure 15 | - | 12 | - | nC |
| Q _{GS(th)} | pre-threshold gate-source charge | | - | 8 | - | nC |
| Q _{GS(th-pl)} | post-threshold gate-source charge | | - | 4 | - | nC |
| Q_{GD} | gate-drain charge | | - | 9.4 | - | nC |
| V _{GS(pI)} | gate-source plateau voltage | V _{DS} = 40 V | - | 4.5 | - | V |
| C _{iss} | input capacitance | $V_{DS} = 12 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ | - | 2782 | - | pF |
| Coss | output capacitance | T _j = 25 °C; see <u>Figure 16</u> | - | 384 | - | pF |
| C _{rss} | reverse transfer capacitance | | - | 162 | - | pF |
| t _{d(on)} | turn-on delay time | $V_{DS} = 12 \text{ V}; R_L = 0.5 \Omega; V_{GS} = 10 \text{ V};$ | - | 19 | - | ns |
| t _r | rise time | $R_{G(ext)} = 4.7 \Omega$ | - | 16 | - | ns |
| t _{d(off)} | turn-off delay time | | - | 33 | - | ns |
| t _f | fall time | | - | 6 | - | ns |
| Source-dra | ain diode | | | | | |
| V_{SD} | source-drain voltage | $I_S = 25 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 \text{ °C}$; see Figure 17 | - | 0.86 | 1.2 | V |
| t _{rr} | reverse recovery time | $I_S = 50 \text{ A}; dI_S/dt = 100 \text{ A/}\mu\text{s};$ | - | 45 | - | ns |
| Q _r | recovered charge | $V_{GS} = 0 \text{ V}; V_{DS} = 40 \text{ V}$ | - | 64 | - | nC |

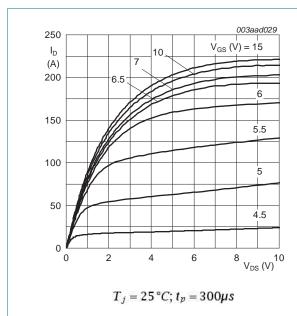


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

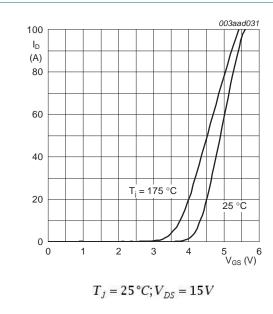
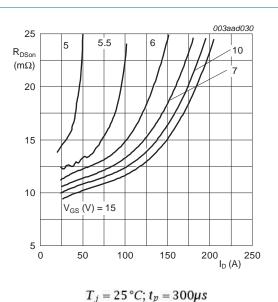
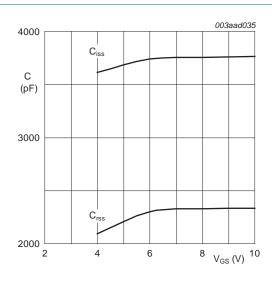


Fig 7. Transfer characteristics: drain current as a function of gate-source voltage; typical values



 $T_j = 23$ C, $t_p = 300\mu$ s

Fig 6. Drain-source on-state resistance as a function of drain current; typical values



 $V_{DS} = 0V; f = 1MHz$

Fig 8. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

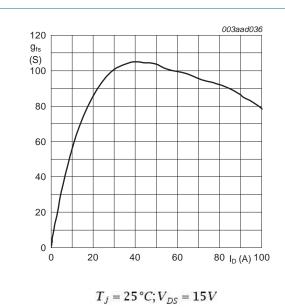


Fig 9. Forward transconductance as a function of drain current; typical values

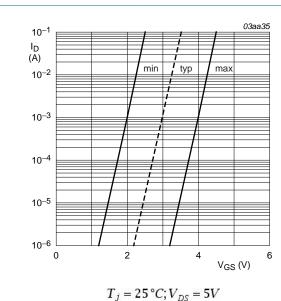
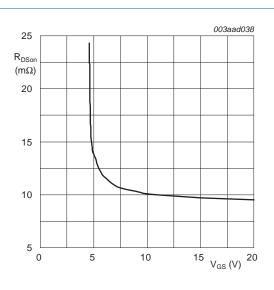
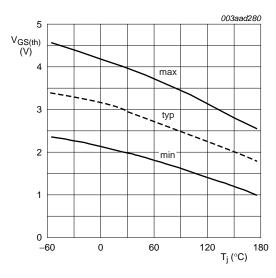


Fig 11. Sub-threshold drain current as a function of gate-source voltage



 $T_j = 25 \,^{\circ}C; I_D = 25A$

Fig 10. Drain-source on-state resistance as a function of gate-source voltage; typical values



 $I_D = 1 \text{ mA}; \ V_{DS} = V_{GS}$

Fig 12. Gate-source threshold voltage as a function of junction temperature

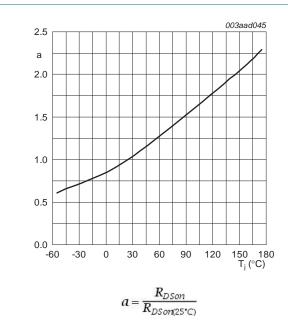


Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

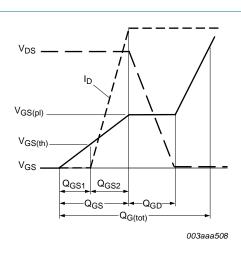


Fig 14. Gate charge waveform definitions

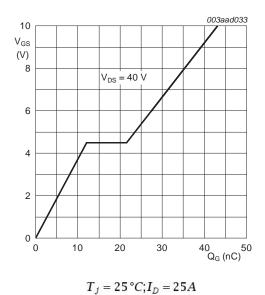
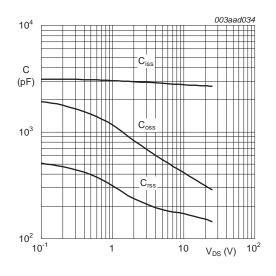


Fig 15. Gate-source voltage as a function of gate

charge; typical values



$$V_{GS} = 0V; f = 1MHz$$

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

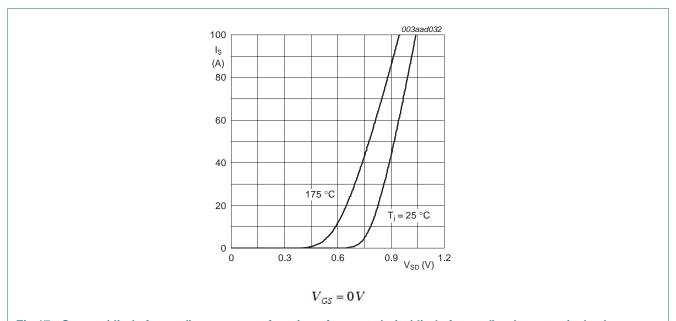


Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

7. Package outline

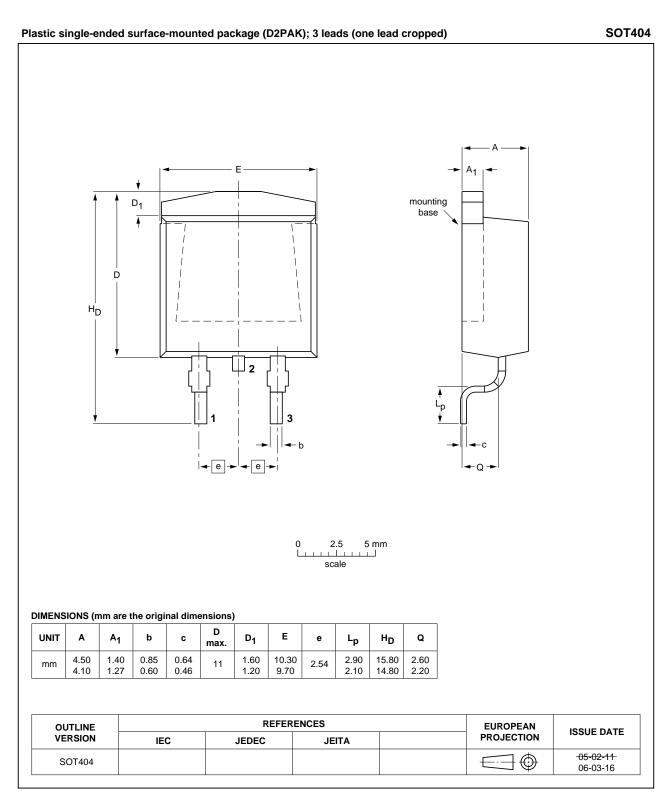


Fig 18. Package outline SOT404 (D2PAK)

8. Revision history

Table 7. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|------------------|------------------------------------|----------------------------|---------------|------------------|
| PSMN012-80BS v.2 | 20120301 | Product data sheet | - | PSMN012-80BS v.1 |
| Modifications: | • | from objective to product. | | |
| | Various change | s to content. | | |
| PSMN012-80BS v.1 | 20111024 | Objective data sheet | - | - |

9. Legal information

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| Document status[1][2] | Product status[3] | Definition |
|--------------------------------|-------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
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| Product [short] data sheet | Production | This document contains the product specification. |

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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Nexperia PSMN012-80BS

N-channel 80 V 11 mΩ standard level MOSFET in D2PAK

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PSMN012-80BS

Nexperia

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